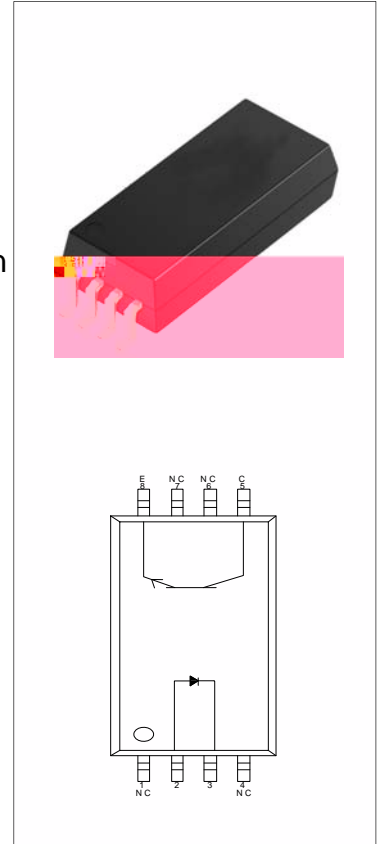


### DESCRIPTION:

The products are transistor opto-couplers in a plastic WSOP8 package. The device which is infrared LED chip and photo-transistor chip is assembled on lead frame, in order to change the electricity-light-electricity. The products are widely used in transmission and conversion of digital logic, power control and switch, electric insulation and impedance conversion between circuits systems.



### MAIN FEATURES

High isolation 7500 VRMS

CTI 600

Operating temperature range -55°C to 110°C

RoHS & REACH Compliance

HBM: H3A; MM: M4; CDM:C3

CQC approved

VDE approved

UL approved

### ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	$I_F$	50	mA
	Peak Forward Current	$I_{FP}$	1	A
	Reverse Voltage	$V_R$	6	V
	Power Dissipation	$P_C$	75	mW
Output	Collector-emitter Voltage	$V_{CEO}$	80	V
	Emitter-collector Voltage	$V_{ECO}$	7	V
	Collector Current	$I_C$	50	mA
	Power Dissipation	$P_C$	150	mW
Total Power Dissipation		$P_{tot}$	2	mW
Isolation Voltage		$V_{iso}$	7500	Vrms
Operating Temperature		$T_{opr}$	-55~+110	
Junction Temperature		$T_j$	125	

Storage Temperature	T <sub>stg</sub>	-55~+125	
Soldering Temperature	T <sub>sol</sub>	260	

NOTE1     μ

NOTE2

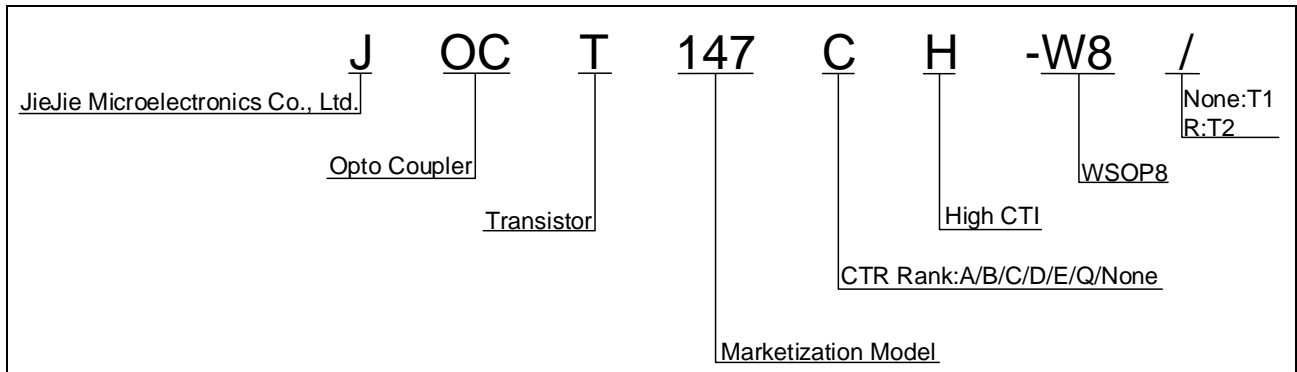
**ELECTRICAL CHARACTERISTICS** (Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =10mA	-	1.2	1.5	V
	Reverse Current	I <sub>R</sub>	V <sub>R</sub> =6V	-	-	1	μA
	Terminal Capacitance	C <sub>t</sub>	V=0,f=1MHz	-	13	-	pF
Output	Collector-Emitter dark current	I <sub>CEO</sub>	V <sub>CE</sub> =20V, I <sub>F</sub> =0	-	-	100	nA
	Collector-Emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> =0.1mA I <sub>F</sub> =0	80	-	-	V
	Emitter-Collector breakdown voltage	BV <sub>ECO</sub>	I <sub>E</sub> =0.1mA I <sub>F</sub> =0	7	-	-	V
Transfer Characteristics	Current transfer ratio	CTR	I <sub>F</sub> =5mA V <sub>CE</sub> =5V	80	-	600	%
	Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>F</sub> =10mA I <sub>C</sub> = 1mA	-	0.06	0.4	V
	Isolation resistance	R <sub>IO</sub>	DC500V 40~60%R.H.	10 <sup>12</sup>	10 <sup>14</sup>	-	
	Floating Capacitance	C <sub>IO</sub>	V=0, f=1MHz	-	0.7	-	pF
	Rise Time	t <sub>r</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =2mA	-	3.5	18	μs
	Fall Time	t <sub>f</sub>	R <sub>L</sub> =100	-	3	18	μs
	Turn On Time	t <sub>on</sub>	V <sub>CC</sub> =5V, I <sub>F</sub> =16mA	-	1.5	-	μs
	Storage Time	t <sub>s</sub>	R <sub>L</sub> =1.9k	-	20	-	μs
Turn Off Time	t <sub>off</sub>		-	35	-	μs	

NOTE1

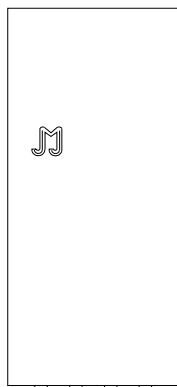
Grade Sign	Min. (%)	Max. (%)

ORDERING INFORMATION



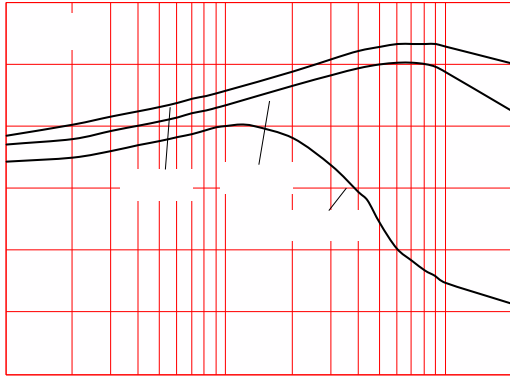
Packing Quantity	
Option	Quantity

MARKING

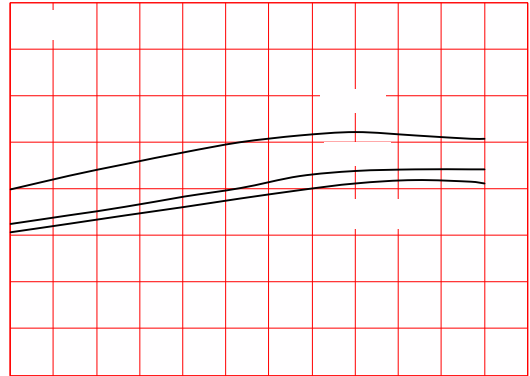




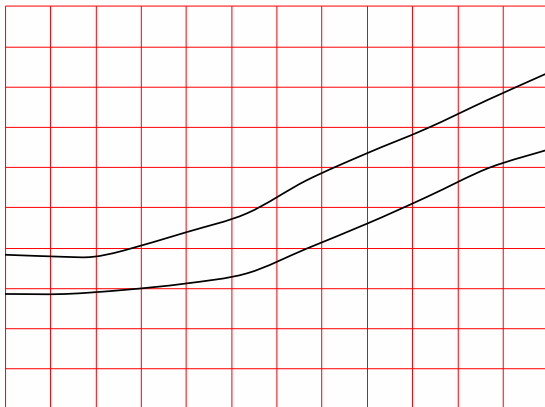
**FIG.7:** Current Transfer Ratio vs. Forward Current



**FIG.8:** Current Transfer Ratio vs. Ambient Temperature



**FIG.9:** Collector-emitter Saturation Voltage vs. Ambient Temperature



**FIG.10:** Response Time vs. Load Resistance

Figure 10 is a graph showing the relationship between Response Time and Load Resistance. The graph is currently blank.

Test Circuits

FIG.12: Test Circuits of Turn On Time

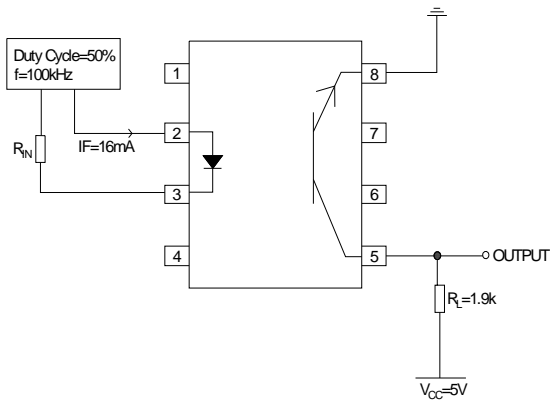
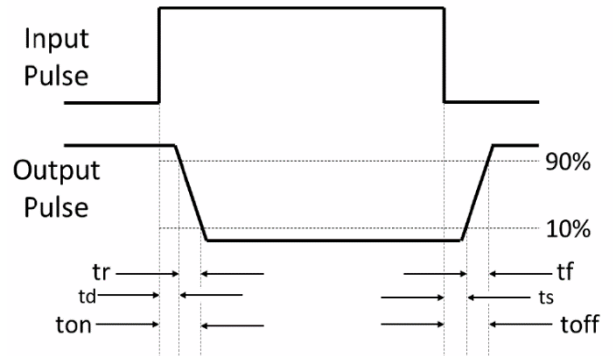
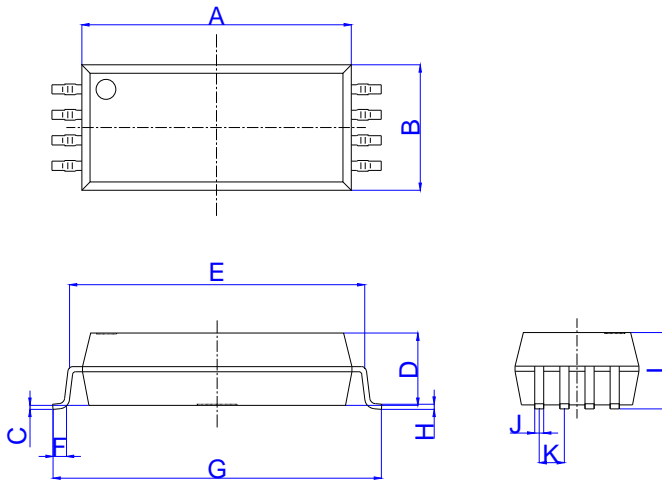


FIG.13: Waveforms of Turn On Time

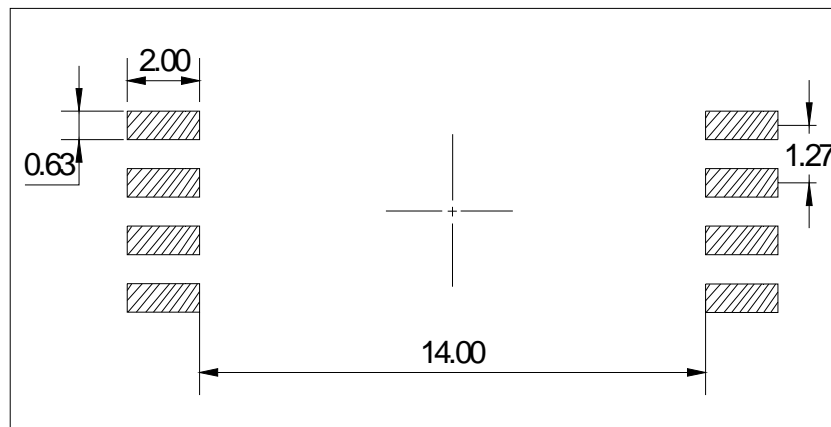


Package Dimension (Unit: mm)

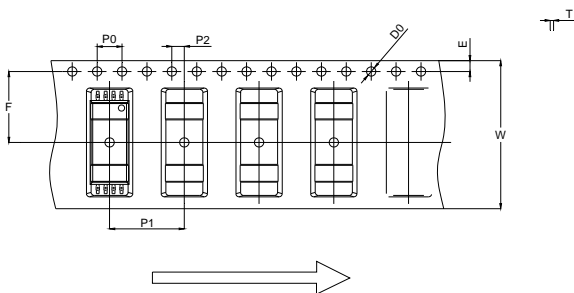


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	13.50		13.70	0.531		0.539
B	6.15		6.35	0.242		0.250
C	0.10		0.30	0.004		0.012
D	3.50		3.70	0.138		0.146
E	14.71		15.31	0.579		0.603
F	0.52		1.02	0.020		0.040
G	16.36		16.86	0.644		0.664
H	0.10		0.40	0.004		0.016
I	3.65		3.95	0.144		0.156
J	0.307		0.607	0.012		0.024
K	1.02		1.52	0.040		0.060

RECOMMENDED SOLDER MASK (Dimensions in mm unless otherwise stated)

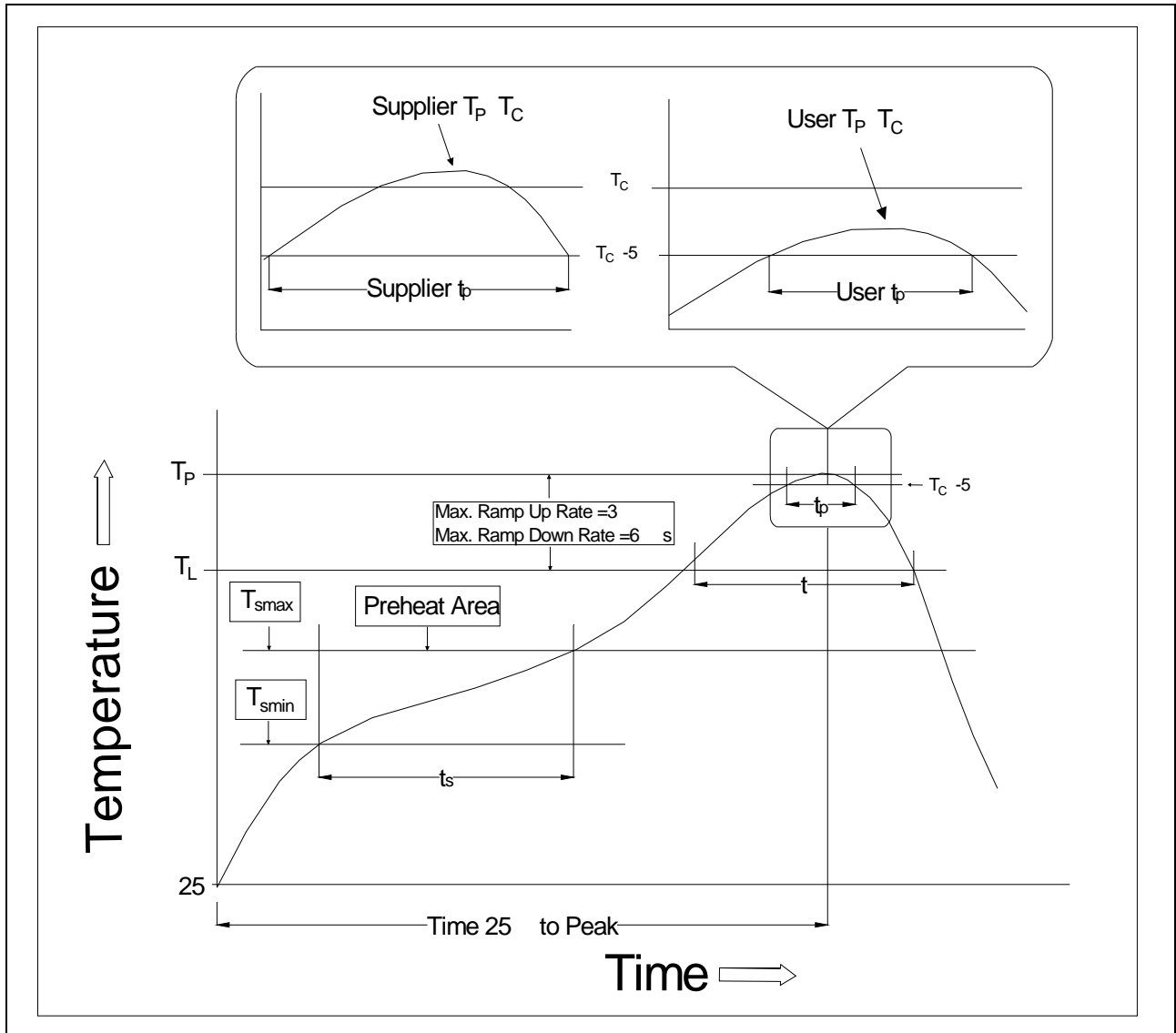


CARRIER TAPE SPECIFICATIONS (Dimensions in mm unless otherwise stated)



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	11.90	12.00	12.10	0.469	0.472	0.476
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	11.40	11.50	11.60	0.449	0.453	0.457
T	0.35	0.40	0.45	0.014	0.016	0.018
W	23.70	24.00	24.30	0.933	0.945	0.957

REFLOW INFORMATION




Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T <sub>min</sub> )	100	150
Temperature Max. (T <sub>max</sub> )	150	200
Time (t <sub>s</sub> ) from (T <sub>min</sub> to T <sub>max</sub> )	60-120 seconds	60-120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3 /second max.	3 /second max.
Liquidus Temperature (T <sub>L</sub> )	183	217
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235 +0 /-5	260 +0 /-5
Time (t <sub>P</sub> ) within 5 of 260	20 seconds	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6 /second max.	6 /second max.
Time 25 to Peak Temperature	6 minutes max.	8 minutes max.

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf life of one year when stored under standard conditions.
6. Recommend storage Temp.: 0~40°C;  
Recommend storage humidity: <60%;  
MSL level: MSL 1

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